



## INFORMATION DISCLOSURE STATEMENT

Applicant : Skarp et al.  
Appl. No. : 10/003,749  
Filed : October 23, 2001  
For : PROCESS FOR PRODUCING  
ALUMINUM OXIDE FILMS AT LOW  
TEMPERATURES  
Examiner : Bret P. Chen  
Group Art Unit : 1762

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

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Dear Sir:

Enclosed is form PTO-1449 listing 7 references that are also enclosed. This Information Disclosure Statement is being filed under 37 C.F.R. § 1.97(c)(2) before the mailing date of a final action and before the mailing of a Notice of Allowance. This Statement is accompanied by the fees set forth in 37 C.F.R. § 1.17(p). The Commissioner is hereby authorized to charge any additional fees which may be required or to credit any overpayment to Account No. 11-1410.

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: October 22, 2003

By: 

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. SEPP15.001AUS	APPLICATION NO. 10/003,749
	APPLICANT Skarp et al.	
	FILING DATE October 23, 2001	GROUP 1762

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1	US 2003/0129298 A1	07/10/03	Tera et al.			
	2	US 2001/0031379 A1	10/18/01	Tera et al.			
	3	US 2002/0003403 A1	01/10/02	Ghosh et al.			
	4	US 2001/0052752 A1	12/20/01	Ghosh et al.			

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	5	WO 03/008110 A1	01/30/03	PCT				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
	6	Kukli et al, "Atomic layer epitaxy growth of aluminum oxide thin films from a novel Al(CH <sub>3</sub> ) <sub>2</sub> Cl precursor and H <sub>2</sub> O.", J. Vac. Sci. Technol. A 15(4), July/Aug 1997, pp. 2214-2218
	7	Hiltunen et al. "Growth and Characterization of Aluminum Oxide Thin Films Deposited from Various Source Materials by Atomic Layer Epitaxy and Chemical Vapor Deposition Processes", Materials Chemistry and Physics, 28 (1991) pp. 379-388
	8	
	9	
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EXAMINER	DATE CONSIDERED
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	